

Electronic Supplementary Information

**Fabrication of Nitrogen-Doped ZnO Nanorod Arrays by
Hydrothermal Synthesis and Ambient Annealing**

Ryosuke Kobayashi,^a Tetsuo Kishi,^a Yuta Katayanagi,^b Tetsuji Yano^a and Nobuhiro Matsushita^{a*}

^a Department of Materials Science and Engineering, School of Materials and Chemical Technology, Tokyo Institute of Technology,
2-12-1 Ookayama, Meguro-ku, Tokyo 152-8550, Japan

^b Department of Technology Education, Faculty of Education, Gunma University,
4-2 Aramaki-machi, Maebashi, Gunma 371-8510, Japan

*Corresponding Author

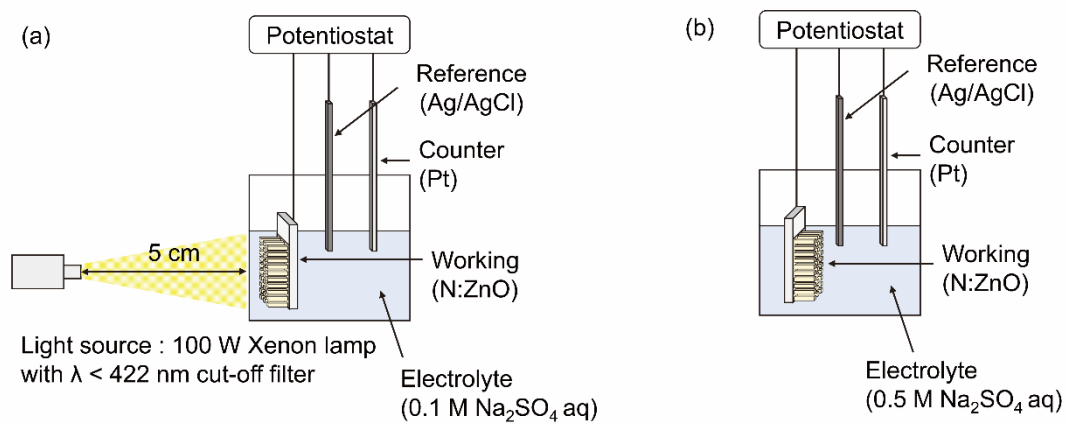


Figure S1 The schematic figures of experimental setups for (a) photocurrent measurements and for (b) electrochemical impedance measurements.

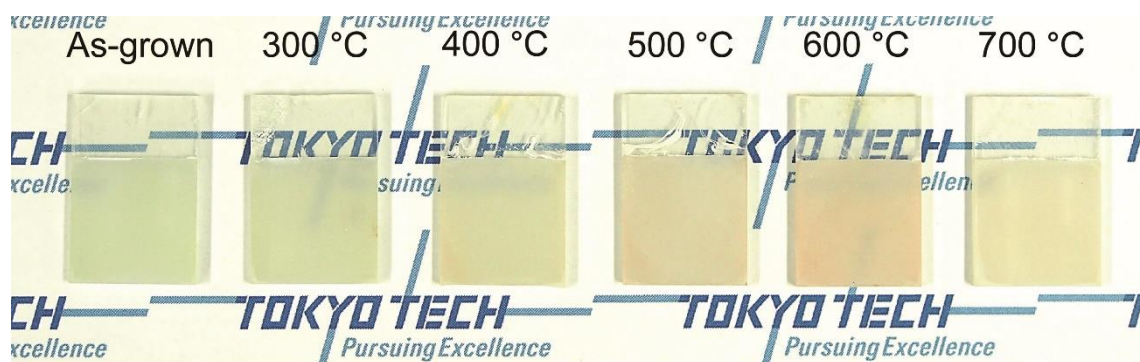


Figure S2 Photographs of N:ZnO NRAs (as-grown, annealed at 300 °C, 400 °C, 500 °C, 600 °C, and 700 °C from left to right).